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Kind regards,

Team Nexperia

# 74LVC4066-Q100

Quad bilateral switch

Rev. 1 — 7 August 2012

Product data sheet

## 1. General description

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The 74LVC4066-Q100 is a high-speed Si-gate CMOS device.

The 74LVC4066-Q100 provides four single pole, single-throw analog switch functions. Each switch has two input/output terminals (nY and nZ) and an active HIGH enable input (nE). When nE is LOW, the analog switch is turned off.

Schmitt-trigger action at the enable inputs makes the circuit tolerant of slower input rise and fall times across the entire  $V_{CC}$  range from 1.65 V to 5.5 V.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

## 2. Features and benefits

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- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - ◆ Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and from  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$
- Wide supply voltage range from 1.65 V to 5.5 V
- Very low ON resistance:
  - ◆  $7.5\ \Omega$  (typical) at  $V_{CC} = 2.7\text{ V}$
  - ◆  $6.5\ \Omega$  (typical) at  $V_{CC} = 3.3\text{ V}$
  - ◆  $6\ \Omega$  (typical) at  $V_{CC} = 5\text{ V}$
- Switch current capability of 32 mA
- High noise immunity
- CMOS low-power consumption
- Direct interface TTL-levels
- Latch-up performance exceeds 250 mA
- ESD protection:
  - ◆ MIL-STD-883, method 3015 exceeds 2000 V
  - ◆ HBM JESD22-A114F exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V ( $C = 200\text{ pF}$ ,  $R = 0\ \Omega$ )
- Enable inputs accept voltages up to 5 V
- Multiple package options

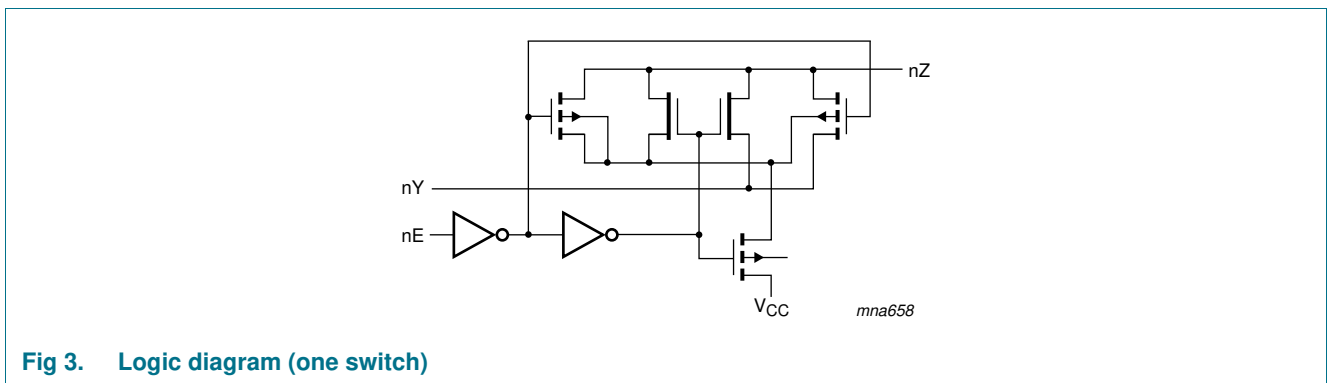
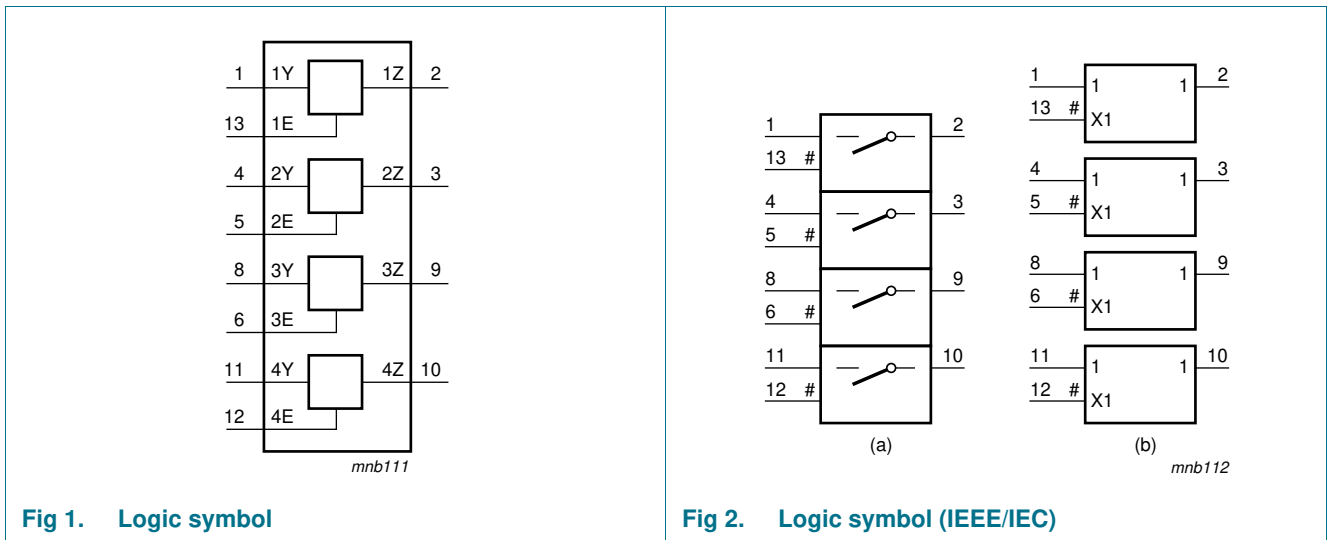


### 3. Ordering information

Table 1. Ordering information

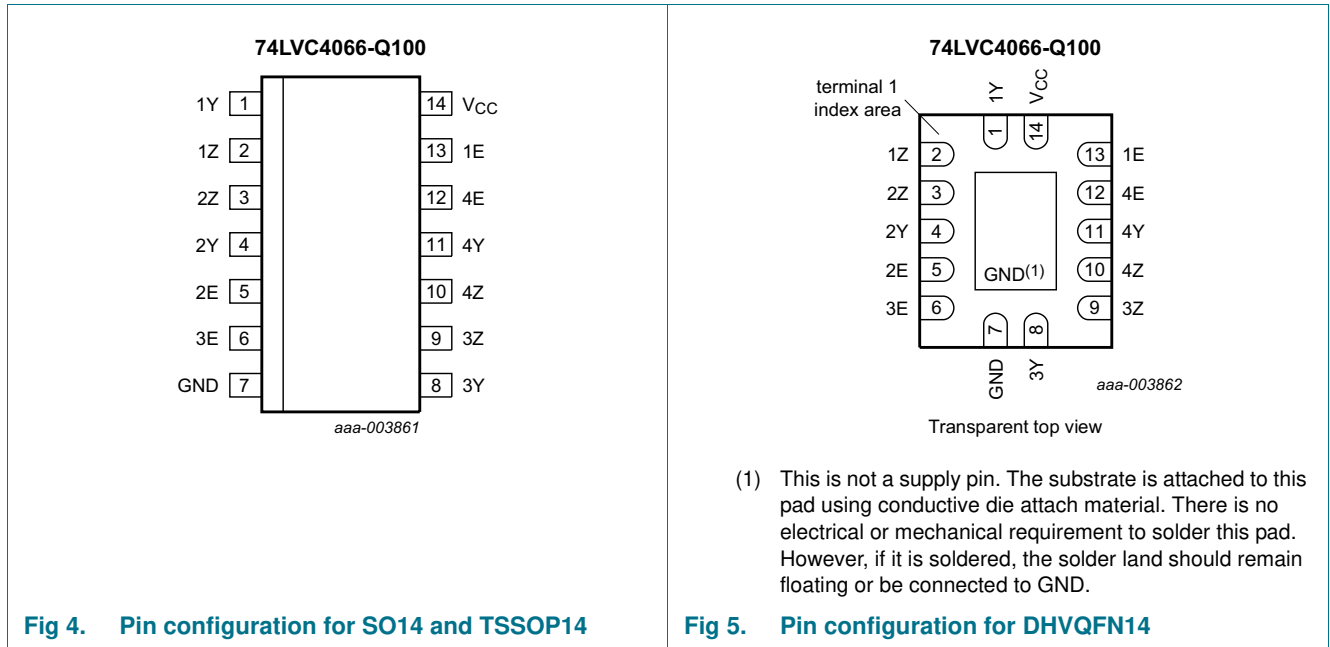
Type number	Package			Version
	Temperature range	Name	Description	
74LVC4066D-Q100	-40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74LVC4066PW-Q100	-40 °C to +125 °C	TSSOP14	plastic thin small outline package; 14 leads; body width 4.4 mm	SOT402-1
74LVC4066BQ-Q100	-40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm	SOT762-1

### 4. Functional diagram



## 5. Pinning information

### 5.1 Pinning



### 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1Y	1	independent input/output
1Z	2	independent output/input
2Z	3	independent output/input
2Y	4	independent input/output
2E	5	enable input (active HIGH)
3E	6	enable input (active HIGH)
GND	7	ground (0 V)
3Y	8	independent input/output
3Z	9	independent output/input
4Z	10	independent output/input
4Y	11	independent input/output
4E	12	enable input (active HIGH)
1E	13	enable input (active HIGH)
V <sub>CC</sub>	14	supply voltage

## 6. Functional description

**Table 3.** Function table<sup>[1]</sup>

Input nE	Switch
L	OFF
H	ON

- [1] H = HIGH voltage level;  
L = LOW voltage level.

## 7. Limiting values

**Table 4.** Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+6.5	V
$V_I$	input voltage		<sup>[1]</sup> -0.5	+6.5	V
$I_{IK}$	input clamping current	$V_I < -0.5\text{ V}$ or $V_I < V_{CC} + 0.5\text{ V}$	-50	-	mA
$I_{SK}$	switch clamping current	$V_I < -0.5\text{ V}$ or $V_I < V_{CC} + 0.5\text{ V}$	-	±50	mA
$V_{SW}$	switch voltage	enable and disable mode	<sup>[2]</sup> -0.5	+6.5	V
$I_{SW}$	switch current	$-0.5 < V_{SW} < V_{CC} + 0.5\text{ V}$	-	±50	mA
$I_{CC}$	supply current		-	100	mA
$I_{GND}$	ground current		-100	-	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$	<sup>[3]</sup> -	500	mW

- [1] The minimum input voltage rating may be exceeded if the input current rating is observed.  
 [2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed.  
 [3] For SO14 packages: above 70 °C derate linearly with 8 mW/K.  
 For TSSOP14 packages: above 60 °C derate linearly with 5.5 mW/K.  
 For DHVQFN14 packages: above 60 °C derate linearly with 4.5 mW/K.

## 8. Recommended operating conditions

**Table 5. Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CC}$	supply voltage		1.65	-	5.5	V
$V_I$	input voltage		0	-	5.5	V
$V_{SW}$	switch voltage		[1] 0	-	$V_{CC}$	V
$T_{amb}$	ambient temperature		-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.65\text{ V to }2.7\text{ V}$	[2] -	-	20	ns/V
		$V_{CC} = 2.7\text{ V to }5.5\text{ V}$	[2] -	-	10	ns/V

[1] To avoid sinking GND current from terminal nZ when switch current flows in terminal nY, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal nZ, no GND current flows from terminal nY. In this case, there is no limit for the voltage drop across the switch.

[2] Applies to control signal levels.

## 9. Static characteristics

**Table 6. Static characteristics**

At recommended operating conditions voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	$0.65V_{CC}$	-	-	$0.65V_{CC}$	-	V
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	1.7	-	-	1.7	-	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	2.0	-	-	2.0	-	V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	$0.7V_{CC}$	-	-	$0.7V_{CC}$	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	-	-	$0.35V_{CC}$	-	$0.35V_{CC}$	V
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	-	-	0.7	-	0.7	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	-	0.8	-	0.8	V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	-	$0.3V_{CC}$	-	$0.3V_{CC}$	V
$I_I$	input leakage current	pin nE; $V_{CC} = 5.5\text{ V}$ ; $V_I = 5.5\text{ V or GND}$ [2]	-	$\pm 0.1$	$\pm 5$	-	$\pm 20$	$\mu\text{A}$
$I_{S(OFF)}$	OFF-state leakage current	$ V_{SW}  = V_{CC} - \text{GND}$ ; $V_{CC} = 5.5\text{ V}$ ; see <a href="#">Figure 6</a> [2]	-	$\pm 0.1$	$\pm 5$	-	$\pm 20$	$\mu\text{A}$
$I_{S(ON)}$	ON-state leakage current	$ V_{SW}  = V_{CC} - \text{GND}$ ; $V_{CC} = 5.5\text{ V}$ ; see <a href="#">Figure 7</a> [2]	-	$\pm 0.1$	$\pm 5$	-	$\pm 20$	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = V_{CC} \text{ or GND}$ ; $V_{SW} = \text{GND or } V_{CC}$ ; $V_{CC} = 5.5\text{ V}$ [2]	-	0.1	10	-	40	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	pin nE; $V_I = V_{CC} - 0.6\text{ V}$ ; $V_{CC} = 5.5\text{ V}$ ; $V_{SW} = \text{GND or } V_{CC}$ [2]	-	5	500	-	5000	$\mu\text{A}$

**Table 6. Static characteristics ...continued**

At recommended operating conditions voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
C <sub>I</sub>	input capacitance		-	12.5	-	-	-	pF
C <sub>S(OFF)</sub>	OFF-state capacitance		-	8.0	-	-	-	pF
C <sub>S(ON)</sub>	ON-state capacitance		-	14.0	-	-	-	pF

- [1] All typical values are measured at T<sub>amb</sub> = 25 °C.
- [2] These typical values are measured at V<sub>CC</sub> = 3.3 V.

### 9.1 Test circuits

V<sub>I</sub> = V<sub>CC</sub> or GND and V<sub>O</sub> = GND or V<sub>CC</sub>.

**Fig 6. Test circuit for measuring OFF-state leakage current**

V<sub>I</sub> = V<sub>CC</sub> or GND and V<sub>O</sub> = open circuit.

**Fig 7. Test circuit for measuring ON-state leakage current**

### 9.2 ON resistance

**Table 7. ON resistance**

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see [Figure 9](#) to [Figure 14](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
R <sub>ON(peak)</sub>	ON resistance (peak)	V <sub>I</sub> = GND to V <sub>CC</sub> ; see <a href="#">Figure 8</a>						
		I <sub>SW</sub> = 4 mA; V <sub>CC</sub> = 1.65 V to 1.95 V	-	34.0	130	-	195	Ω
		I <sub>SW</sub> = 8 mA; V <sub>CC</sub> = 2.3 V to 2.7 V	-	12.0	30	-	45	Ω
		I <sub>SW</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	10.4	25	-	38	Ω
		I <sub>SW</sub> = 24 mA; V <sub>CC</sub> = 3 V to 3.6 V	-	7.8	20	-	30	Ω
		I <sub>SW</sub> = 32 mA; V <sub>CC</sub> = 4.5 V to 5.5 V	-	6.2	15	-	23	Ω



**Table 7. ON resistance ...continued**

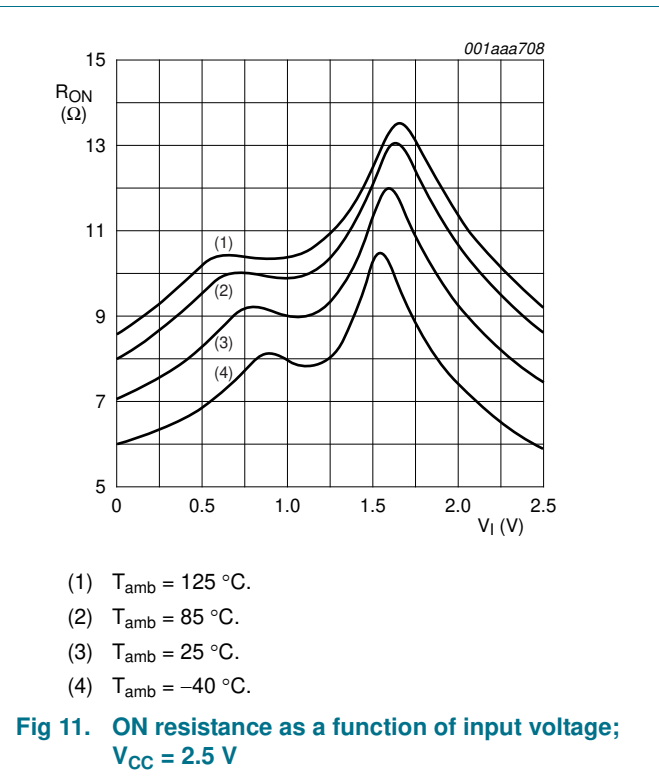
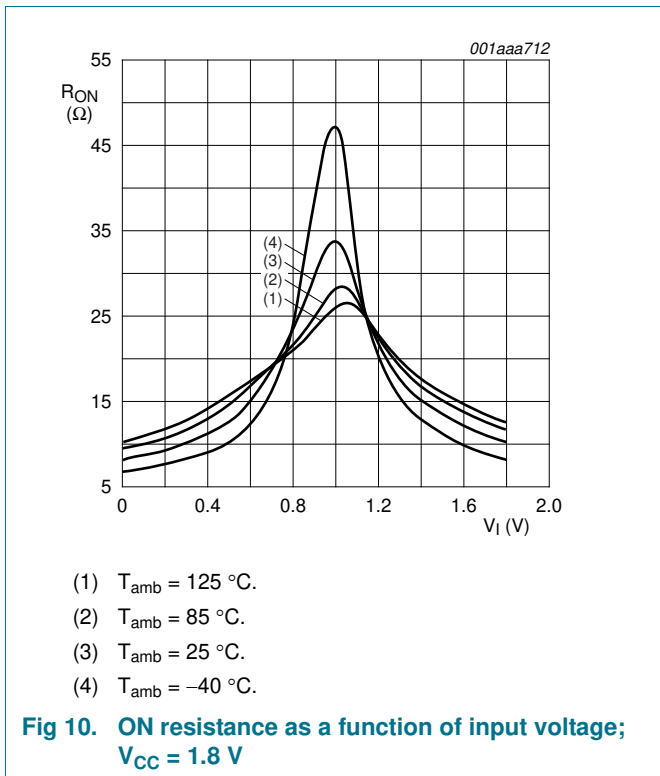
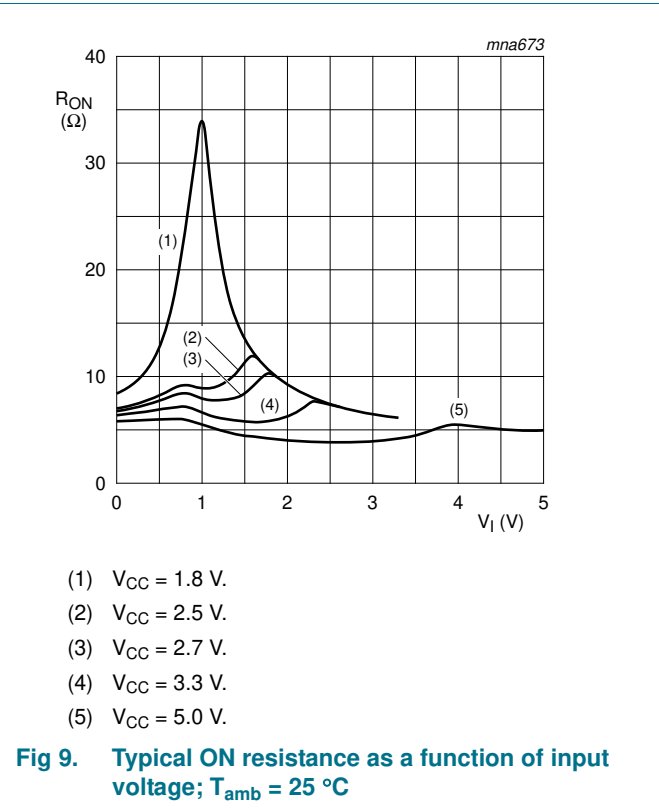
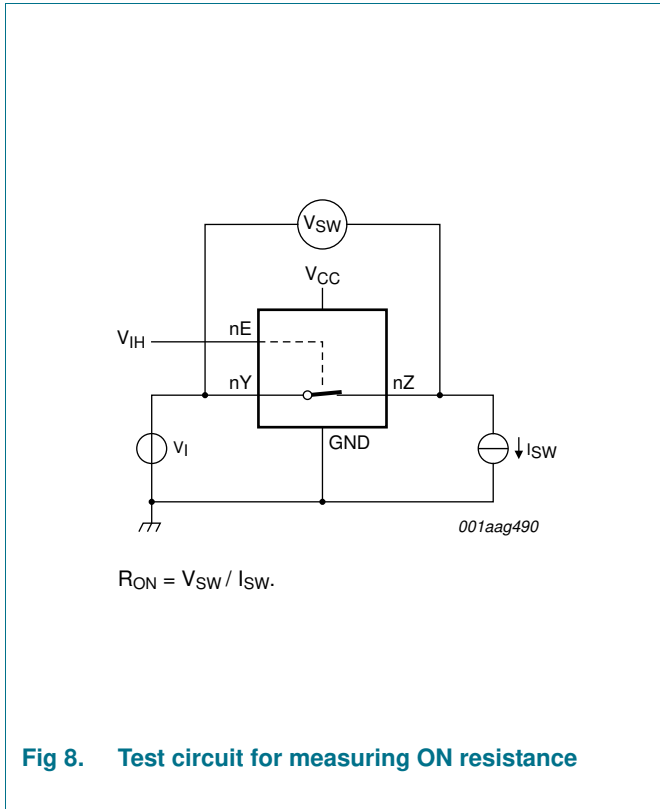
At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graphs see [Figure 9](#) to [Figure 14](#).

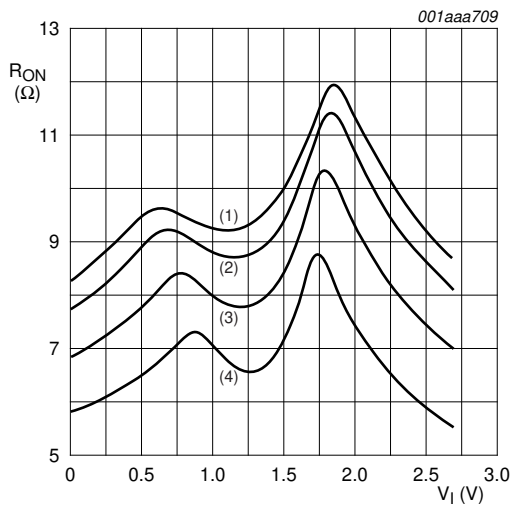
Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
R <sub>ON(rail)</sub>	ON resistance (rail)	V <sub>I</sub> = GND; see <a href="#">Figure 8</a>						
		I <sub>SW</sub> = 4 mA; V <sub>CC</sub> = 1.65 V to 1.95 V	-	8.2	18	-	27	Ω
		I <sub>SW</sub> = 8 mA; V <sub>CC</sub> = 2.3 V to 2.7 V	-	7.1	16	-	24	Ω
		I <sub>SW</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	6.9	14	-	21	Ω
		I <sub>SW</sub> = 24 mA; V <sub>CC</sub> = 3 V to 3.6 V	-	6.5	12	-	18	Ω
		I <sub>SW</sub> = 32 mA; V <sub>CC</sub> = 4.5 V to 5.5 V	-	5.8	10	-	15	Ω
		V <sub>I</sub> = V <sub>CC</sub> ; see <a href="#">Figure 8</a>						
		I <sub>SW</sub> = 4 mA; V <sub>CC</sub> = 1.65 V to 1.95 V	-	10.4	30	-	45	Ω
		I <sub>SW</sub> = 8 mA; V <sub>CC</sub> = 2.3 V to 2.7 V	-	7.6	20	-	30	Ω
		I <sub>SW</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	7.0	18	-	27	Ω
		I <sub>SW</sub> = 24 mA; V <sub>CC</sub> = 3 V to 3.6 V	-	6.1	15	-	23	Ω
		I <sub>SW</sub> = 32 mA; V <sub>CC</sub> = 4.5 V to 5.5 V	-	4.9	10	-	15	Ω
R <sub>ON(flat)</sub>	ON resistance (flatness)	V <sub>I</sub> = GND to V <sub>CC</sub> <a href="#">[2]</a>						
		I <sub>SW</sub> = 4 mA; V <sub>CC</sub> = 1.65 V to 1.95 V	-	26.0	-	-	-	Ω
		I <sub>SW</sub> = 8 mA; V <sub>CC</sub> = 2.3 V to 2.7 V	-	5.0	-	-	-	Ω
		I <sub>SW</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	3.5	-	-	-	Ω
		I <sub>SW</sub> = 24 mA; V <sub>CC</sub> = 3 V to 3.6 V	-	2.0	-	-	-	Ω
		I <sub>SW</sub> = 32 mA; V <sub>CC</sub> = 4.5 V to 5.5 V	-	1.5	-	-	-	Ω

[1] Typical values are measured at T<sub>amb</sub> = 25 °C and nominal V<sub>CC</sub>.

[2] Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical V<sub>CC</sub> and temperature.

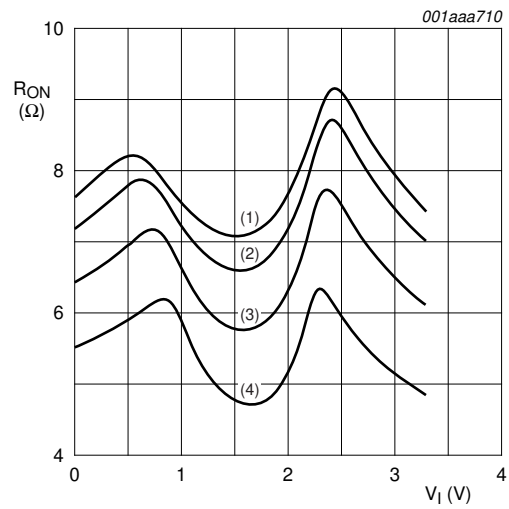
9.3 ON resistance test circuit and graphs





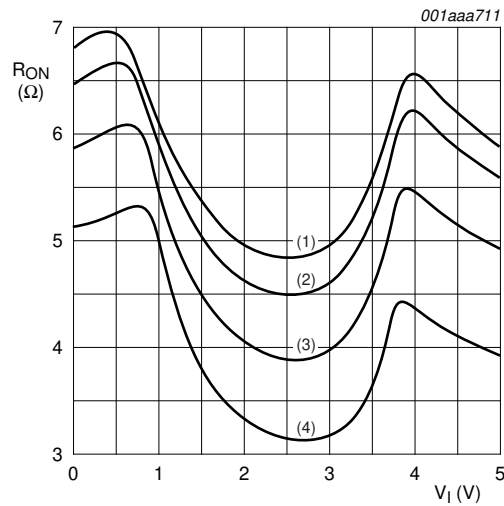
- (1)  $T_{amb} = 125$  °C.
- (2)  $T_{amb} = 85$  °C.
- (3)  $T_{amb} = 25$  °C.
- (4)  $T_{amb} = -40$  °C.

**Fig 12. ON resistance as a function of input voltage;  $V_{CC} = 2.7$  V**



- (1)  $T_{amb} = 125$  °C.
- (2)  $T_{amb} = 85$  °C.
- (3)  $T_{amb} = 25$  °C.
- (4)  $T_{amb} = -40$  °C.

**Fig 13. ON resistance as a function of input voltage;  $V_{CC} = 3.3$  V**



- (1)  $T_{amb} = 125$  °C.
- (2)  $T_{amb} = 85$  °C.
- (3)  $T_{amb} = 25$  °C.
- (4)  $T_{amb} = -40$  °C.

**Fig 14. ON resistance as a function of input voltage;  $V_{CC} = 5.0$  V**

## 10. Dynamic characteristics

**Table 8. Dynamic characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit [Figure 17](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
t <sub>pd</sub>	propagation delay	nY to nZ or nZ to nY; see <a href="#">Figure 15</a> <sup>[2][3]</sup>						
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	0.8	2.0	-	3.0	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	0.4	1.2	-	2.0	ns
		V <sub>CC</sub> = 2.7 V	-	0.4	1.0	-	1.5	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	0.3	0.8	-	1.5	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	0.2	0.6	-	1.0	ns
t <sub>en</sub>	enable time	nE to nY or nZ; see <a href="#">Figure 16</a> <sup>[4]</sup>						
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.0	5.3	10	1.0	12.5	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.0	3.0	5.6	1.0	7.0	ns
		V <sub>CC</sub> = 2.7 V	1.0	2.6	5.0	1.0	6.5	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.0	2.5	4.4	1.0	5.5	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	1.0	1.9	3.9	1.0	5.0	ns
t <sub>dis</sub>	disable time	nE to nY or nZ; see <a href="#">Figure 16</a> <sup>[5]</sup>						
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.0	4.2	9.0	1.0	11.5	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.0	2.4	5.5	1.0	7.0	ns
		V <sub>CC</sub> = 2.7 V	1.0	3.6	6.5	1.0	8.5	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.0	3.4	6.0	1.0	7.5	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	1.0	2.5	5.0	1.0	6.5	ns
C <sub>PD</sub>	power dissipation capacitance	C <sub>L</sub> = 50 pF; f <sub>i</sub> = 10 MHz; V <sub>I</sub> = GND to V <sub>CC</sub> <sup>[6]</sup>						
		V <sub>CC</sub> = 2.5 V	-	11.0	-	-	-	pF
		V <sub>CC</sub> = 3.3 V	-	12.5	-	-	-	pF
		V <sub>CC</sub> = 5.0 V	-	15.6	-	-	-	pF

[1] Typical values are measured at T<sub>amb</sub> = 25 °C and nominal V<sub>CC</sub>.

[2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.

[3] Propagation delay is the calculated RC time constant of the typical ON resistance of the switch and the specified capacitance when driven by an ideal voltage source (zero output impedance).

[4] t<sub>en</sub> is the same as t<sub>PZH</sub> and t<sub>PZL</sub>.

[5] t<sub>dis</sub> is the same as t<sub>PLZ</sub> and t<sub>PHZ</sub>.

[6] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum\{(C_L + C_{S(ON)}) \times V_{CC}^2 \times f_o\}$$

where:

f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

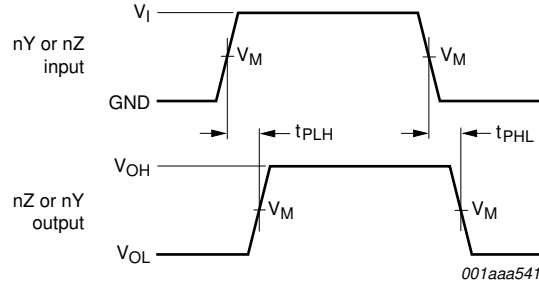
C<sub>S(ON)</sub> = maximum ON-state switch capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

∑{(C<sub>L</sub> + C<sub>S(ON)</sub>) × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>} = sum of the outputs.

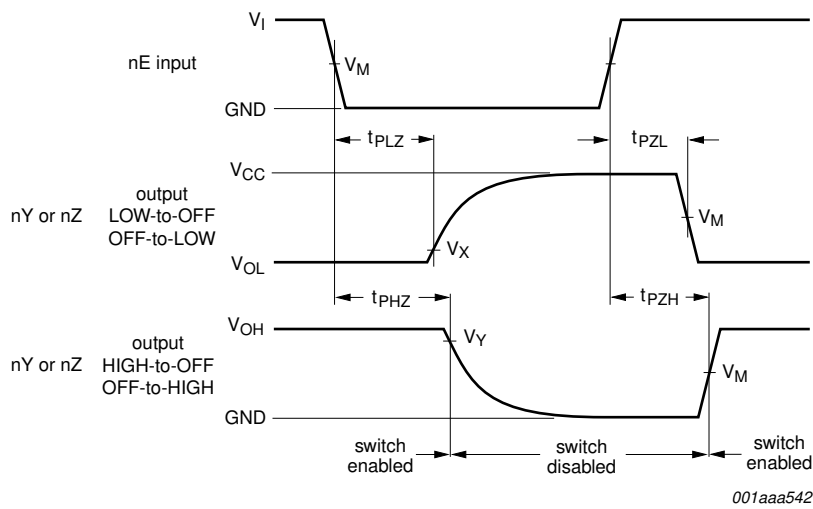
10.1 Waveforms and test circuit



Measurement points are given in [Table 9](#).

Logic levels: VOL and VOH are typical output voltage levels that occur with the output load.

Fig 15. Input (nY or nZ) to output (nZ or nY) propagation delays



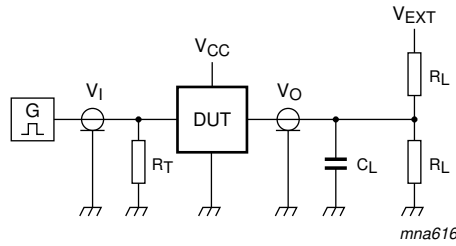
Measurement points are given in [Table 9](#).

Logic levels: VOL and VOH are typical output voltage levels that occur with the output load.

Fig 16. Enable and disable times

Table 9. Measurement points

Supply voltage	Input	Output		
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>
1.65 V to 1.95 V	0.5V <sub>CC</sub>	0.5 V <sub>CC</sub>	V <sub>OL</sub> + 0.15 V	V <sub>OH</sub> - 0.15 V
2.3 V to 2.7 V	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>	V <sub>OL</sub> + 0.15 V	V <sub>OH</sub> - 0.15 V
2.7 V	1.5 V	1.5 V	V <sub>OL</sub> + 0.3 V	V <sub>OH</sub> - 0.3 V
3.0 V to 3.6 V	1.5 V	1.5 V	V <sub>OL</sub> + 0.3 V	V <sub>OH</sub> - 0.3 V
4.5 V to 5.5 V	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>	V <sub>OL</sub> + 0.3 V	V <sub>OH</sub> - 0.3 V



Test data is given in [Table 10](#).

Definitions test circuit:

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_L$  = Load resistance.

$V_{EXT}$  = External voltage for measuring switching times.

**Fig 17. Load circuit for switching times**

**Table 10. Test data**

Supply voltage	Input		Load		$V_{EXT}$		
$V_{CC}$	$V_I$	$t_r, t_f$	$C_L$	$R_L$	$t_{PLH}, t_{PHL}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
1.65 V to 1.95 V	$V_{CC}$	$\leq 2.0$ ns	30 pF	1 k $\Omega$	open	GND	$2V_{CC}$
2.3 V to 2.7 V	$V_{CC}$	$\leq 2.0$ ns	30 pF	500 $\Omega$	open	GND	$2V_{CC}$
2.7 V	2.7 V	$\leq 2.5$ ns	50 pF	500 $\Omega$	open	GND	6 V
3.0 V to 3.6 V	2.7 V	$\leq 2.5$ ns	50 pF	500 $\Omega$	open	GND	6 V
4.5 V to 5.5 V	$V_{CC}$	$\leq 2.5$ ns	50 pF	500 $\Omega$	open	GND	$2V_{CC}$

## 10.2 Additional dynamic characteristics

**Table 11. Additional dynamic characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V);  $T_{amb} = 25$  °C.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
THD	total harmonic distortion	$R_L = 10$ k $\Omega$ ; $C_L = 50$ pF; $f_i = 1$ kHz; see <a href="#">Figure 18</a>				
		$V_{CC} = 1.65$ V	-	0.032	-	%
		$V_{CC} = 2.3$ V	-	0.008	-	%
		$V_{CC} = 3$ V	-	0.006	-	%
		$V_{CC} = 4.5$ V	-	0.005	-	%
		$R_L = 10$ k $\Omega$ ; $C_L = 50$ pF; $f_i = 10$ kHz; see <a href="#">Figure 18</a>				
		$V_{CC} = 1.65$ V	-	0.068	-	%
		$V_{CC} = 2.3$ V	-	0.009	-	%
		$V_{CC} = 3$ V	-	0.008	-	%
		$V_{CC} = 4.5$ V	-	0.006	-	%

**Table 11. Additional dynamic characteristics ...continued**At recommended operating conditions; voltages are referenced to GND (ground = 0 V);  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .

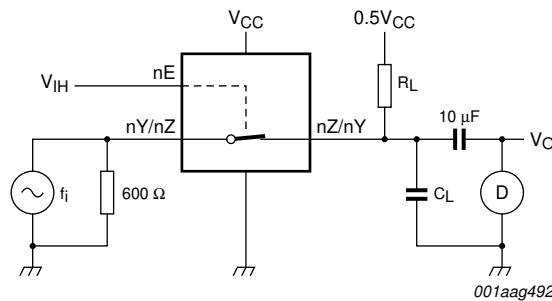
Symbol	Parameter	Conditions	Min	Typ	Max	Unit		
$f_{ -3\text{dB}}$	-3 dB frequency response	$R_L = 600\ \Omega$ ; $C_L = 50\ \text{pF}$ ; see <a href="#">Figure 19</a>						
		$V_{CC} = 1.65\ \text{V}$	-	170	-	MHz		
		$V_{CC} = 2.3\ \text{V}$	-	210	-	MHz		
		$V_{CC} = 3\ \text{V}$	-	212	-	MHz		
		$V_{CC} = 4.5\ \text{V}$	-	215	-	MHz		
		$R_L = 50\ \Omega$ ; $C_L = 5\ \text{pF}$ ; see <a href="#">Figure 19</a>						
		$V_{CC} = 1.65\ \text{V}$	-	> 500	-	MHz		
		$V_{CC} = 2.3\ \text{V}$	-	> 500	-	MHz		
		$V_{CC} = 3\ \text{V}$	-	> 500	-	MHz		
		$V_{CC} = 4.5\ \text{V}$	-	> 500	-	MHz		
		$\alpha_{\text{iso}}$	isolation (OFF-state)	$R_L = 600\ \Omega$ ; $C_L = 50\ \text{pF}$ ; $f_i = 1\ \text{MHz}$ ; see <a href="#">Figure 20</a>				
				$V_{CC} = 1.65\ \text{V}$	-	-46	-	dB
$V_{CC} = 2.3\ \text{V}$	-			-46	-	dB		
$V_{CC} = 3\ \text{V}$	-			-46	-	dB		
$V_{CC} = 4.5\ \text{V}$	-			-46	-	dB		
$R_L = 50\ \Omega$ ; $C_L = 5\ \text{pF}$ ; $f_i = 1\ \text{MHz}$ ; see <a href="#">Figure 20</a>								
$V_{CC} = 1.65\ \text{V}$	-			-42	-	dB		
$V_{CC} = 2.3\ \text{V}$	-			-42	-	dB		
$V_{CC} = 3\ \text{V}$	-			-42	-	dB		
$V_{CC} = 4.5\ \text{V}$	-			-42	-	dB		
$V_{\text{ct}}$	crosstalk voltage			between digital inputs and switch; $R_L = 600\ \Omega$ ; $C_L = 50\ \text{pF}$ ; $f_i = 1\ \text{MHz}$ ; $t_r = t_f = 2\ \text{ns}$ ; see <a href="#">Figure 21</a>				
				$V_{CC} = 1.65\ \text{V}$	-	69	-	mV
		$V_{CC} = 2.3\ \text{V}$	-	87	-	mV		
		$V_{CC} = 3\ \text{V}$	-	156	-	mV		
		$V_{CC} = 4.5\ \text{V}$	-	302	-	mV		
Xtalk	crosstalk	between switches; $R_L = 600\ \Omega$ ; $C_L = 50\ \text{pF}$ ; $f_i = 1\ \text{MHz}$ ; see <a href="#">Figure 22</a>						
		$V_{CC} = 1.65\ \text{V}$	-	-58	-	dB		
		$V_{CC} = 2.3\ \text{V}$	-	-58	-	dB		
		$V_{CC} = 3\ \text{V}$	-	-58	-	dB		
		$V_{CC} = 4.5\ \text{V}$	-	-58	-	dB		
		between switches; $R_L = 50\ \Omega$ ; $C_L = 5\ \text{pF}$ ; $f_i = 1\ \text{MHz}$ ; see <a href="#">Figure 22</a>						
		$V_{CC} = 1.65\ \text{V}$	-	-58	-	dB		
		$V_{CC} = 2.3\ \text{V}$	-	-58	-	dB		
		$V_{CC} = 3\ \text{V}$	-	-58	-	dB		
		$V_{CC} = 4.5\ \text{V}$	-	-58	-	dB		

**Table 11. Additional dynamic characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V);  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$Q_{inj}$	charge injection	$C_L = 0.1\text{ nF}$ ; $V_{gen} = 0\text{ V}$ ; $R_{gen} = 0\text{ }\Omega$ ; $f_i = 1\text{ MHz}$ ; $R_L = 1\text{ M}\Omega$ ; see <a href="#">Figure 23</a>				
		$V_{CC} = 1.8\text{ V}$	-	3.3	-	pC
		$V_{CC} = 2.5\text{ V}$	-	4.1	-	pC
		$V_{CC} = 3.3\text{ V}$	-	5.0	-	pC
		$V_{CC} = 4.5\text{ V}$	-	6.4	-	pC
		$V_{CC} = 5.5\text{ V}$	-	7.5	-	pC

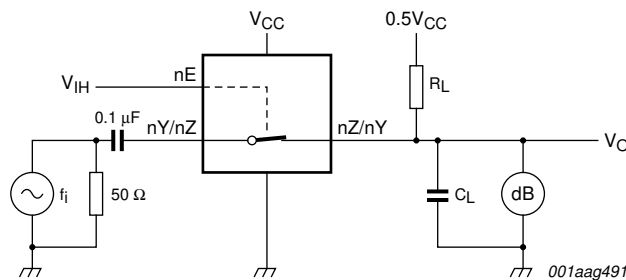
**10.2.1 Test circuits**



**Test conditions:**

- $V_{CC} = 1.65\text{ V}$ :  $V_i = 1.4\text{ V}$  (p-p).
- $V_{CC} = 2.3\text{ V}$ :  $V_i = 2\text{ V}$  (p-p).
- $V_{CC} = 3\text{ V}$ :  $V_i = 2.5\text{ V}$  (p-p).
- $V_{CC} = 4.5\text{ V}$ :  $V_i = 4\text{ V}$  (p-p).

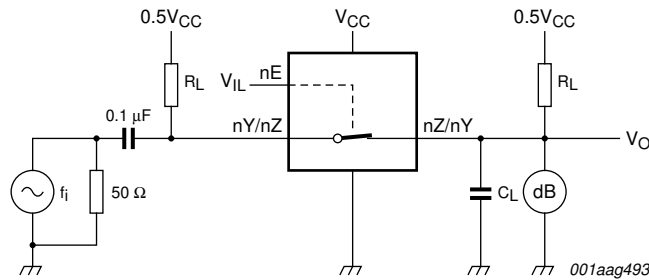
**Fig 18. Test circuit for measuring total harmonic distortion**



Adjust  $f_i$  voltage to obtain 0 dBm level at output. Increase  $f_i$  frequency until dB meter reads -3 dB.

**Fig 19. Test circuit for measuring the frequency response when switch is in ON-state**





Adjust  $f_i$  voltage to obtain 0 dBm level at input.

Fig 20. Test circuit for measuring isolation (OFF-state)

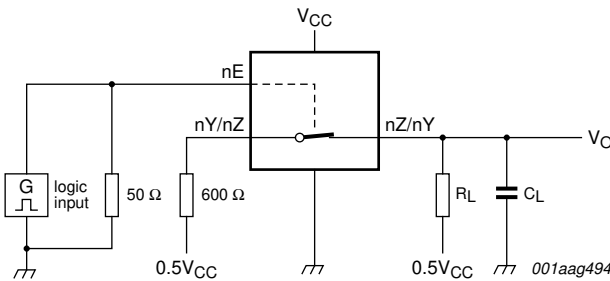
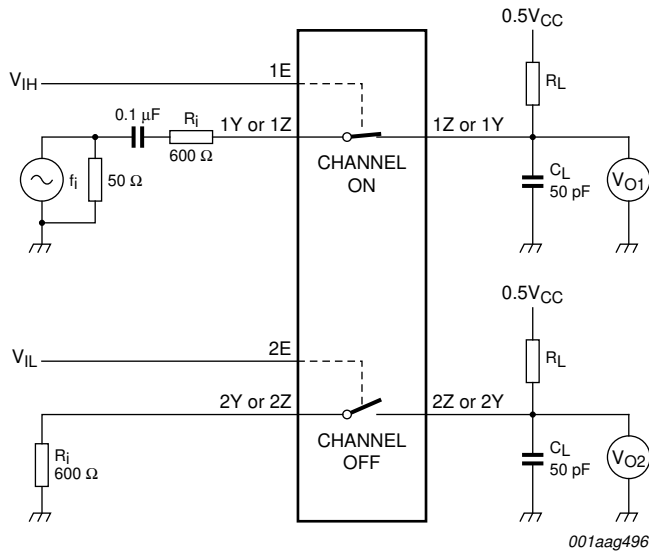
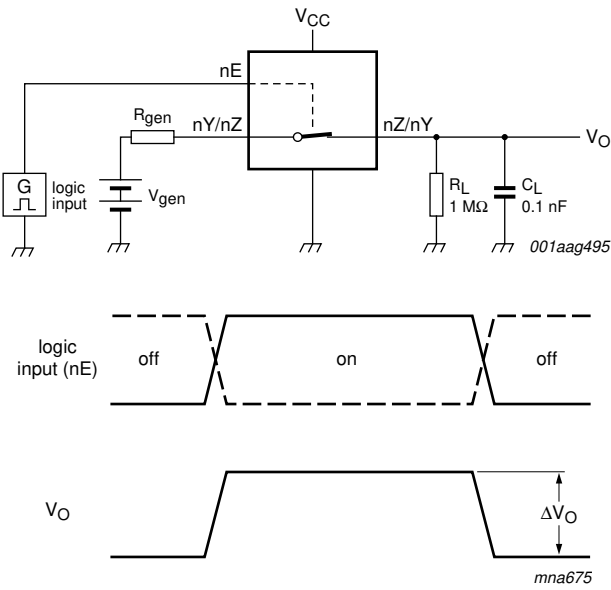


Fig 21. Test circuit for measuring crosstalk voltage (between digital inputs and switch)



$20 \log_{10} (V_{O2} / V_{O1})$  or  $20 \log_{10} (V_{O1} / V_{O2})$ .

Fig 22. Test circuit for measuring crosstalk between switches



$Q_{inj} = \Delta V_O \times C_L$ .  
 $\Delta V_O$  = output voltage variation.  
 $R_{gen}$  = generator resistance.  
 $V_{gen}$  = generator voltage.

**Fig 23. Test circuit for measuring charge injection**

11. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

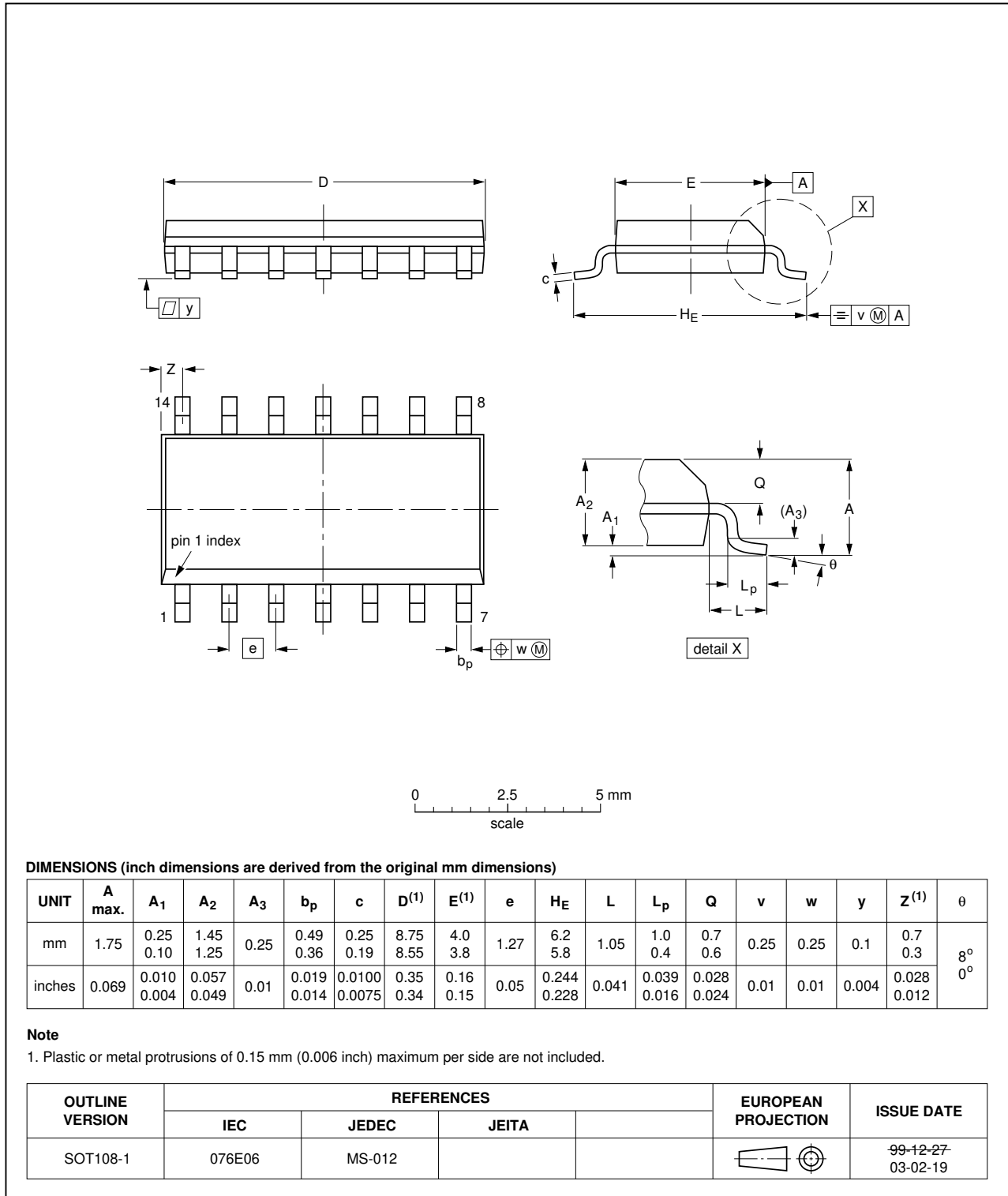


Fig 24. Package outline SOT108-1 (SO14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

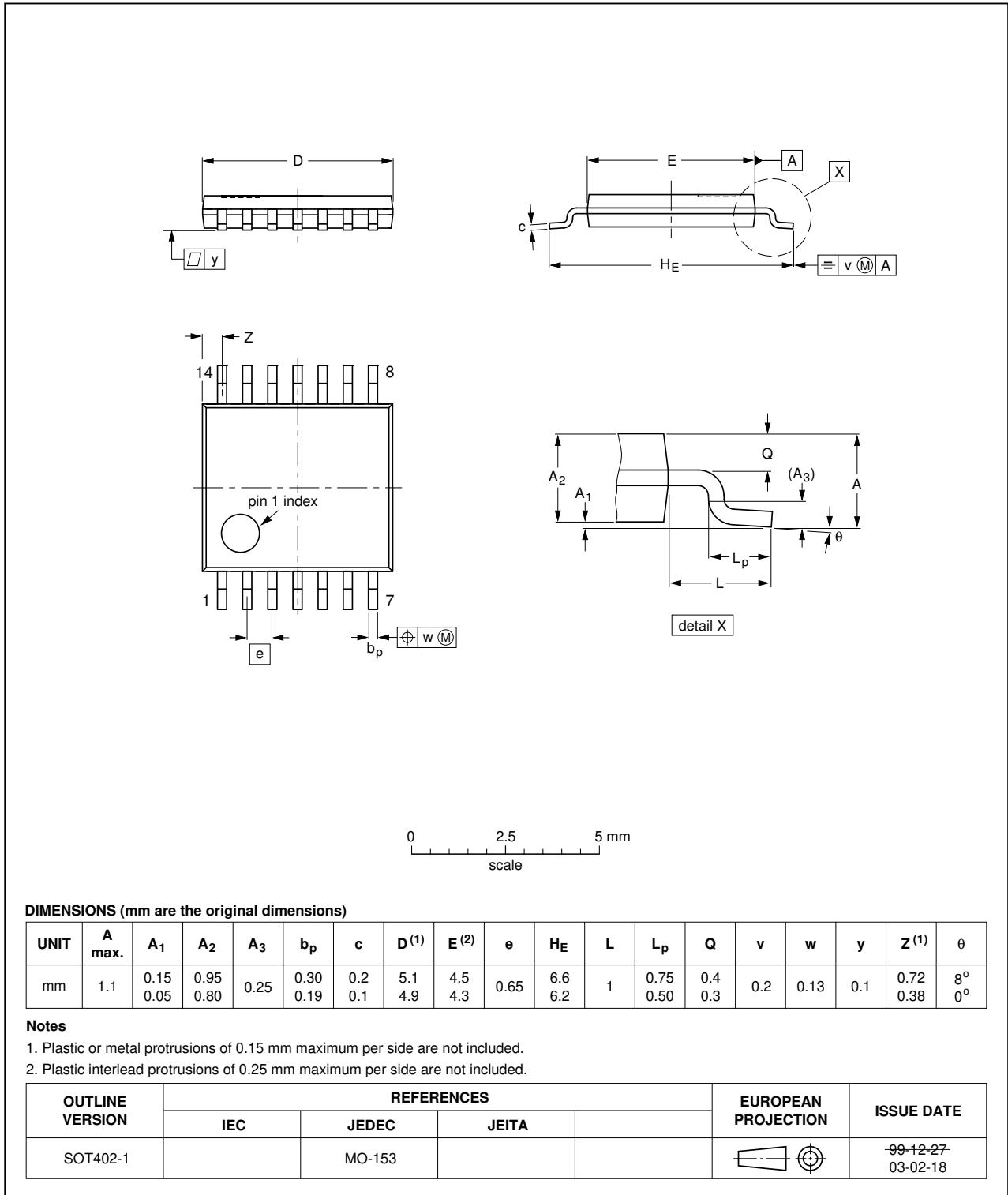


Fig 25. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm

SOT762-1

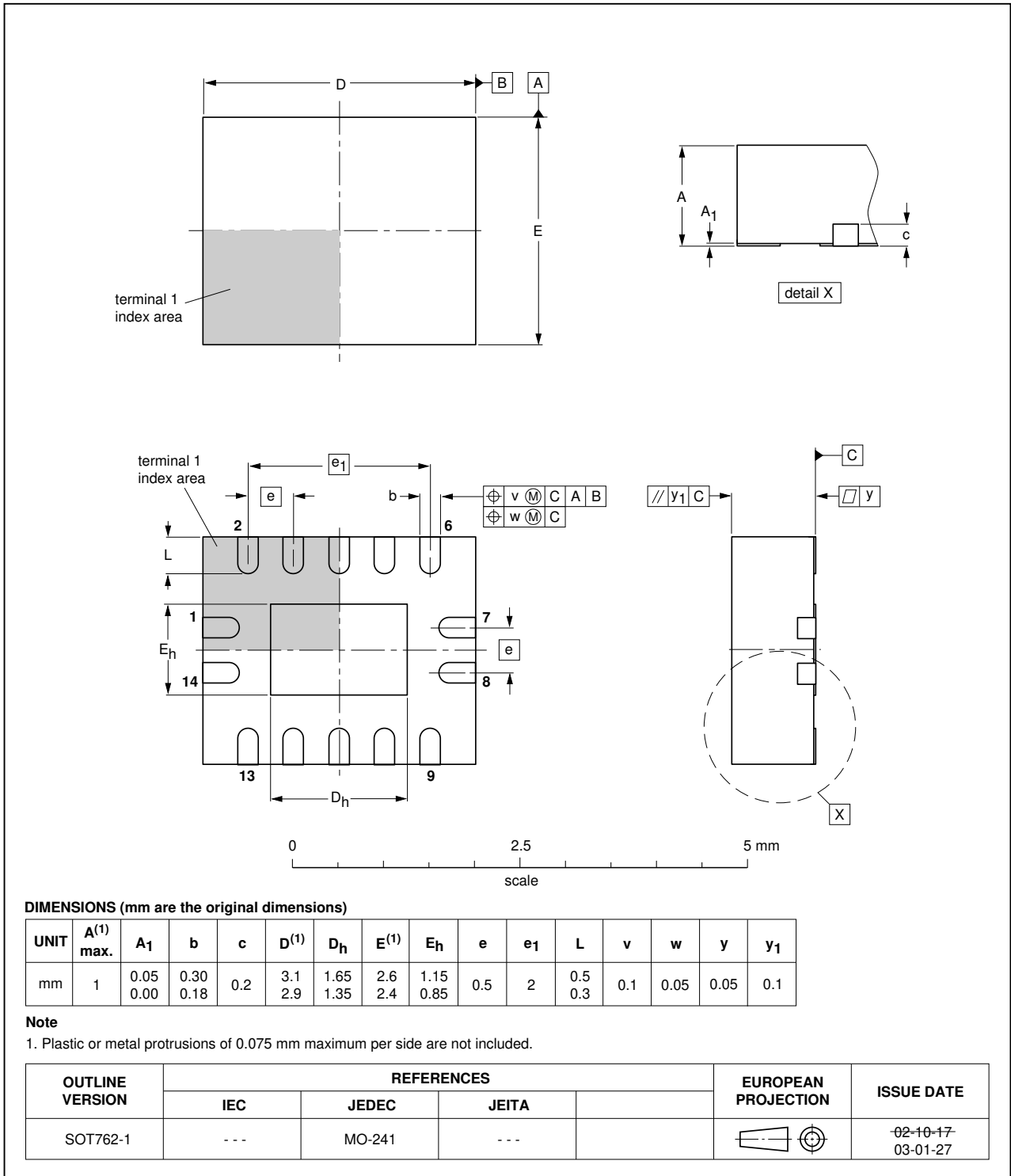


Fig 26. Package outline SOT762-1 (DHVQFN14)

## 12. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
DUT	Device Under Test
MIL	Military

## 13. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC4066_Q100 v.1	20120807	Product data sheet	-	-

## 14. Legal information

### 14.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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